

ABSTRACT OF THE DISCLOSURE

There is provided a semiconductor device including a transistor formed by means of a common contact hole that connects a gate electrode, and a diffused layer forming a source/drain terminal; and a semiconductor device comprising the gate electrode of the transistor, and a connecting terminal to which capacitance between substrates and capacitance between the gate electrode and the source/drain terminal are added, thereby improving the soft error resistance caused by alpha rays and neutron beams.

100-200-300-400-500-600-700-800-900